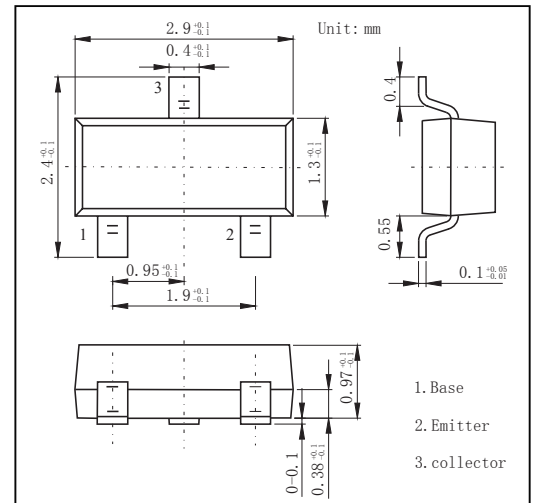


SOT-23 Plastic-Encapsulate Transistors
Features

- For general amplification
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector - Base Voltage	V_{CBO}	-45	V
Collector - Emitter Voltage	V_{CEO}	-45	
Emitter - Base Voltage	V_{EBO}	-7	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-45			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -2 mA, I_B = 0$	-45			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-7			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -40 V, I_E = 0$			-0.1	uA
Collector-Emitter cut-off current	I_{CEO}	$V_{CE} = -20 V, I_B = 0$			-100	
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -10V, I_C = -2mA$	160		460	
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			2.7	pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA, f = 200MHz$	60			MHz

RATINGS AND CHARACTERISTIC CURVES

